

## Amendments to the Claims

1. (Currently Amended) A method of forming a semiconductor structure, comprising:

providing a first and a second material;

processing the first material to form a portion of the semiconductor structure; and

detecting a condition of the second material to determine whether processing of the first material is complete;

wherein the second material comprises a substance provided on the first material, wherein the substance includes a tag having the detectable condition.

2. (Cancelled).

3. (Cancelled).

4. (Currently Amended) The method of claim 3 1, wherein the processing comprises removing a portion of the first material.

5. (Original) The method of claim 4, wherein the processing further comprises removing the second material having the detectable condition, and wherein processing of the first material is complete upon complete removal of the second material.

6. (Original) The method of claim 1, wherein processing of the first material is incomplete if the detectable condition of the second material is detected.

7. (Original) The method of claim 6, further comprising, if the processing of the first material is incomplete: continuing the processing of the first material; detecting the condition of the second material; and repeating the processing and detecting steps until the detectable condition of the second material is not detected.

8. (Cancelled).

9. (Cancelled).

10. (Original) The method of claim 1, wherein the processing comprises chemical-mechanical polishing (CMP).

11. (Cancelled).

12. (Cancelled).

13. (Currently Amended) The method of claim ~~42~~ 1, wherein the processing of the first material is complete when the detectable condition of the tag is detected only on areas of the semiconductor device selected from the group consisting of: expected areas of the first material, expected areas of another material of the semiconductor structure, and no areas on the semiconductor structure.

14. (Currently Amended) The method of claim ~~42~~ 1, wherein the detectable condition of the tag comprises fluorescence.

15. (Currently Amended) The method of claim ~~42~~ 1, wherein the tag comprises a fluorescent molecule that provides the detectable condition, and wherein the fluorescent molecule binds to a material selected from the group consisting of: the first material and another material of the semiconductor structure.

16. (Currently Amended) A semiconductor structure for detecting completion of processing of a material, comprising: a sacrificial layer formed below the material, the sacrificial layer having a detectable condition, wherein the material comprises a liner for interconnects in a wiring level.

17. (Original) The semiconductor structure of claim 16, wherein the sacrificial layer comprises a fluorescent film, and wherein the detectable condition comprises fluorescence.

18. (Cancelled).

19. (Currently Amended) A semiconductor structure for detecting completion of processing of a material, comprising:

a sacrificial layer formed below the material, the sacrificial layer having a detectable condition ~~The semiconductor structure of claim 16,~~

wherein the sacrificial layer is selected from the group consisting of ~~comprising~~: europium thenoyltrifluoroacetate (EuTTA); chelates of La, Sm, Eu, Gd, Lu, Yb, Tb, Dy or Tm; and ~~or~~ (beta)-diketone chelates including Eu benzoylacetate, Eu dibenzoylmethide or Eu hexafluoroacetate.

20. (Cancelled).